INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

OIPE JAN 23 2004 PATENT & TRADEMARK OFFICE

Docket Number (Optional)	Application Number
PTGF-03068	10/694,760
Applicant(s) Toshiya Uemura	
Filing Date October 29, 2003	**Group Art Unit** Not Yet Assigned

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation YES	Translation NO
TTN		2001-267242	09/28/2001	Japan	—	—	✓	

OTHER DOCUMENTS *(Including Author, Title, Date, Pertinent Pages, Etc.)*

TTN		Kazuyuki Tadatomo, et al., "High Output Power InGaN Ultraviolet Light-Emitting Diodes Fabricated on Patterned Substrates Using Metalorganic Vapor Phase Epitaxy", Japanese Journal Appl. Phys. Vol 40., Part 2, No. 6B, June 15, 2001, pp. L583-585.

EXAMINER _____ **DATE CONSIDERED** 02/01/2005

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.